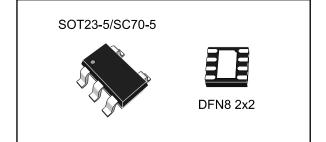


TS3011

Rail-to-rail high-speed comparator

Datasheet - production data



Features

- Propagation delay: 8 ns
- Low current consumption: 470 µA typ. at 5 V
- Rail-to-rail inputs
- Push-pull outputs
- Supply operation from 2.2 to 5 V
- Wide temperature range: -40 °C to 125 °C
- ESD tolerance: 2 kV HBM/200 V MM
- Latch-up immunity: 200 mA
- SMD packages
- Automotive qualification

Applications

- Telecoms
- Instrumentation
- Signal conditioning
- High-speed sampling systems
- Portable communication systems

Description

The TS3011 single comparator features a highspeed response time with rail-to-rail inputs. Specified for a supply voltage of 2.2 to 5 V, this comparator can operate over a wide temperature range from -40 °C to 125 °C.

The TS3011 offers micropower consumption as low as a few hundred microamperes, thus providing an excellent ratio of power consumption current versus response time.

The TS3011 includes push-pull outputs and is available in tiny packages to overcome space constraints.

This is information on a product in full production.

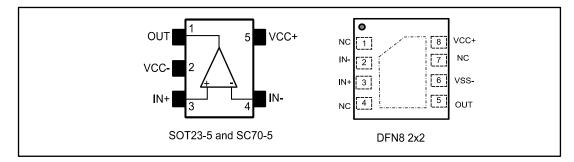
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1 Pin configuration





2 Absolute maximum ratings and operating conditions

Table 1: Absolute maximum ratings								
Symbol	Parameter		Value	Unit				
Vcc	Supply voltage ⁽¹⁾	5.5						
Vid	Differential input voltage ⁽²⁾	±5	V					
V _{IN}	Input voltage range	(V_{CC}) - 0.3 to (V_{CC}) + 0.3						
D	Thermel registeres junction to embient (3)	SOT23-5	250					
Rthja	Thermal resistance junction-to-ambient ⁽³⁾	SC70-5	205	°C/W				
D	Thermel registeres junction to appa (3)	SOT23-5	81					
RTHJC	Thermal resistance junction-to-case ⁽³⁾	SC70-5	172					
T _{STG}	Storage temperature	-65 to 150						
TJ	Junction temperature		150	°C				
TLEAD	Lead temperature (soldering 10 seconds)		260					
	Human body model (HBM) ⁽⁴⁾	2000						
	Machine model (MM) ⁽⁵⁾	200	V					
ESD	Charged device model (CDM) (6)	SOT23-5	1500	V				
	Charged device model (CDM) ⁽⁶⁾	SC70-5	1300					
	Latch-up immunity	200	mA					

Table 1: Absolute maximum ratings

Notes:

 $^{(1)}\mbox{All}$ voltage values, except the differential voltage, are referenced to Vcc^{-} .

⁽²⁾The magnitude of input and output voltages must never exceed the supply rail ±0.3 V.

⁽³⁾Short-circuits can cause excessive heating. These values are typical.

 $^{(4)}$ Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5 k Ω resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.

⁽⁵⁾Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins are floating.

⁽⁶⁾Charged device model: all pins and package are charged together to the specified voltage and then discharged directly to ground.

Symbol	Parameter	Value	Unit
Toper	Operating temperature range	-40 to 125	°C
Vcc	Supply voltage (V_{CC^+} - V_{CC^-}), -40 °C < T_{amb} < 125 °C	2.2 to 5	
VICM	Common mode input voltage range, -40 °C < T _{amb} < 125 °C	(V _{CC} ⁻) - 0.2 to (V _{CC} ⁺) + 0.2	V



TS3011

3 Electrical characteristics

In the electrical characteristic tables below, all values over the temperature range are guaranteed through correlation and simulation. No production tests are performed at the temperature range limits.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
	lenut effect veltere (1)		-7	-0.2	7		
Vio	Input offset voltage ⁽¹⁾	-40 °C < T _{amb} < 125 °C	-8		8	mV	
ΔVio	Input offset voltage drift	-40 °C < T _{amb} < 125 °C		5	20	µV/°C	
V _{HYST}	Input hysteresis voltage (2)			2		mV	
lua -	Input offset current ⁽³⁾			1	20		
lio		-40 °C < T _{amb} < 125 °C			100	D A	
lus.	Input bias current			1	20	рА	
IB	Input bias current	-40 °C < T _{amb} < 125 °C			100		
		No load, output high		0.52	0.64		
	Current	No load, output high, -40 °C < T _{amb} < 125 °C			0.9		
Icc	Supply current	No load, output low		0.65	0.88		
		No load, output low, -40 °C < T _{amb} < 125 °C			1.1	mA	
	Short circuit current	Source	14	18			
lsc		Sink	11	14			
	Output voltage high	I _{source} = 4 mA	1.94	1.97		V	
V _{он}		-40 °C < T _{amb} < 125 °C	1.85			V	
Max		I _{sink} = 4 mA		150	190	— mV	
Vol	Output voltage low	-40 °C < T _{amb} < 125 °C			250		
CMRR	Common-mode rejection ratio	0 < V _{ICM} < 2.7 V	50	68		dB	
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 5 mV		16			
TPLH	Propagation delay, low to high output level ⁽⁴⁾	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 15 mV		12			
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 50 mV		10	15		
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 5 mV		16			
T _{PHL}	Propagation delay, high to low output level ⁽⁵⁾	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 15 mV		12		ns	
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 50 mV		10	15		
T _R	Rise time (10 % to 90 %)	$\label{eq:cl} \begin{split} C_L &= 12 \text{ pF}, R_L = 1 M\Omega, \\ \text{overdrive} &= 100 \text{mV} \end{split}$		3.0			
TF	Fall time (90 % to 10 %)	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 100 mV		2.5			

Table 3: VCC = 2.2 V, VICM = VCC/2, T_{amb} = 25 °C (unless otherwise specified)



Electrical characteristics

Notes:

⁽¹⁾The offset is defined as the average value of positive (V_{TRIP+}) and negative (V_{TRIP-}) trip points (input voltage differences) requested to change the output state in each direction.

⁽²⁾Hysteresis is a built-in feature of the TS3011. It is defined as the voltage difference between the trip points.

⁽³⁾Maximum values include unavoidable inaccuracies of the industrial tests.

 $^{(4)}$ Overdrive is measured with reference to the V_{TRIP+} point.

 $^{(5)}\mbox{Overdrive}$ is measured with reference to the $V_{\mbox{TRIP-}}$ point.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit	
V	Input offect veltage (1)		-7	-0.1	7		
V _{IO}	Input offset voltage ⁽¹⁾	-40 °C < T _{amb} < 125 °C	-9		9	mV	
ΔVιο	Input offset voltage drift	-40 °C < T _{amb} < 125 °C		5	20	μV/°C	
VHYST	Input hysteresis voltage (2)			2		mV	
lio	Input offect current (3)			1	20		
ΠΟ	Input offset current ⁽³⁾	-40 °C < T _{amb} < 125 °C			100	pА	
IIB	Input bias current			1	20	рд	
ΠB		-40 °C < T _{amb} < 125 °C			100		
		No load, output high		0.52	0.65		
l	Supply ourrept	No load, output high, -40 °C < T _{amb} < 125 °C			0.9		
Icc	Supply current	No load, output low		0.66	0.89	- m^	
		No load, output low, -40 °C < T _{amb} < 125 °C			1.1	mA	
	Short circuit current	Source	24	27			
lsc		Sink	19	22			
Vон	Output voltage high	I _{source} = 4 mA	2.48	2.52		V	
VOH		-40 °C < T _{amb} < 125 °C	2.40				
	Output voltage low	I _{sink} = 4 mA		130	170		
V _{OL}		-40 °C < T _{amb} < 125 °C			220	mV	
CMRR	Common-mode rejection ratio	0 < V _{ICM} < 2.7 V	52	70		dB	
		$\label{eq:CL} \begin{split} C_L &= 12 \text{ pF}, R_L = 1 M\Omega, \\ \text{overdrive} &= 5 mV \end{split}$		16			
T _{PLH}	Propagation delay, low to high output level ⁽⁴⁾	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 15 mV		11		ns	
		$\label{eq:cl} \begin{array}{l} C_L = 12 \; pF, \; R_L = 1 \; M\Omega, \\ overdrive = 50 \; mV \end{array}$		9	13		
		$\label{eq:cl} \begin{array}{l} C_L = 12 \; pF, \; R_L = 1 \; M\Omega, \\ overdrive = 5 \; mV \end{array}$		16		ns	
T _{PHL}	Propagation delay, high to low output level ⁽⁵⁾	$\label{eq:cl} \begin{array}{l} C_L = 12 \; pF, \; R_L = 1 \; M\Omega, \\ overdrive = 15 \; mV \end{array}$		11		- 115	
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 50 mV		9	13		

Table 4: VCC = 2.7 V, VICM = VCC/2, Tamb = 25 °C (unless otherwise specified)



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Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
T _R	Rise time (10 % to 90 %)	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 100 mV		2.3		ns
TF	Fall time (90 % to 10 %)	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 100 mV		1.8		110

Notes:

 $^{(1)}$ The offset is defined as the average value of positive (V_{TRIP+}) and negative (V_{TRIP-}) trip points (input voltage differences) requested to change the output state in each direction.

⁽²⁾Hysteresis is a built-in feature of the TS3011. It is defined as the voltage difference between the trip points.

⁽³⁾Maximum values include unavoidable inaccuracies of the industrial tests.

 $^{\rm (4)} Overdrive is measured with reference to the V_{TRIP+} point.$

 $^{(5)}\mbox{Overdrive}$ is measured with reference to the $V_{\mbox{TRIP-}}$ point.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit		
	length offerst veltere (1)		-7	-0.4	7			
V _{IO}	Input offset voltage ⁽¹⁾	-40 °C < T _{amb} < 125 °C	-9		9	— mV		
ΔV_{IO}	Input offset voltage drift	-40 °C < T _{amb} < 125 °C		10	30	µV/°C		
V _{HYST}	Input hysteresis voltage (2)			2		mV		
l	Input offect ourrent (3)			1	20			
lio	Input offset current ⁽³⁾	-40 °C < T _{amb} < 125 °C			100	~^		
	Input biog ourrent			1	20	рА		
I _{IB}	Input bias current	-40 °C < T _{amb} < 125 °C			100			
		No load, output high		0.47	0.69			
	Supply current	No load, output high, -40 °C < T _{amb} < 125 °C			0.9			
lcc		No load, output low		0.60	0.91	mA		
		No load, output low, -40 °C < T _{amb} < 125 °C			1.1	ША		
1	Chart airquit aurrant	Source	58	62		1		
lsc	Short circuit current	Sink	58	64				
N/		I _{source} = 4 mA	4.84	4.89		v		
Vон	Output voltage high	-40 °C < T _{amb} < 125 °C	4.80					
Max		I _{sink} = 4 mA		90	120			
Vol	Output voltage low	-40 °C < T _{amb} < 125 °C			180	mV		
CMRR	Common-mode rejection ratio	0 < V _{ICM} < 2.7 V	57	74		dB		
SVR	Supply voltage rejection	$\Delta V_{CC} = 2.2 \text{ V to 5 V}$		79		uБ		
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 5 mV		14		ns		
T _{PLH}	Propagation delay, low to high output level ⁽⁴⁾	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 15 mV		10				
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 50 mV		8	11			

Table 5: VCC = 5 V, VICM = VCC/2, Tamb = 25 °C (unless otherwise specified)



Electrical characteristics

TS3011

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 5 mV		16		
T _{PHL}	Propagation delay, high to low output level ⁽⁵⁾	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 15 mV		11		
		$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 50 mV		9	12	ns
T _R	Rise time (10 % to 90 %)	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 100 mV		1.1		
TF	Fall time (90 % to 10 %)	$C_L = 12 \text{ pF}, R_L = 1 \text{ M}\Omega,$ overdrive = 100 mV		1.0		

Notes:

 $^{(1)}$ The offset is defined as the average value of positive (V_{TRIP+}) and negative (V_{TRIP-}) trip points (input voltage differences) requested to change the output state in each direction.

⁽²⁾Hysteresis is a built-in feature of the TS3011. It is defined as the voltage difference between the trip points.

⁽³⁾Maximum values include unavoidable inaccuracies of the industrial tests.

 $^{(4)}\mbox{Overdrive}$ is measured with reference to the $V_{\mbox{TRIP+}}$ point.

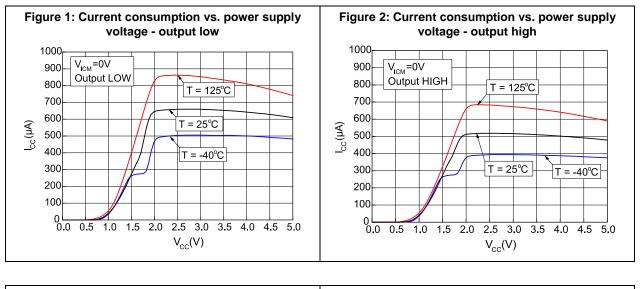
 $^{(5)}\mbox{Overdrive}$ is measured with reference to the $V_{\mbox{TRIP-}}$ point.

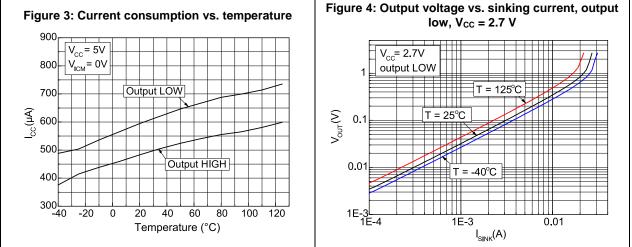




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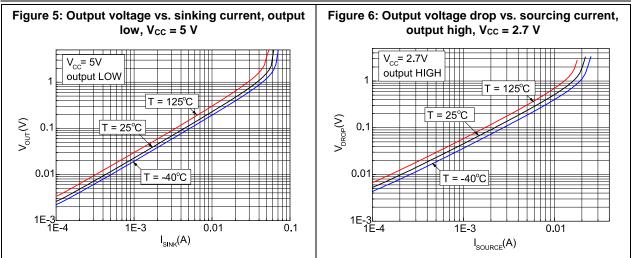
Electrical characteristic curves

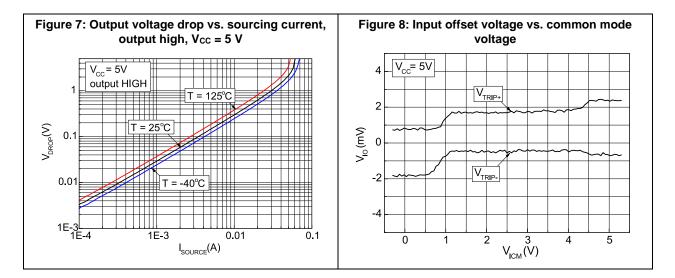


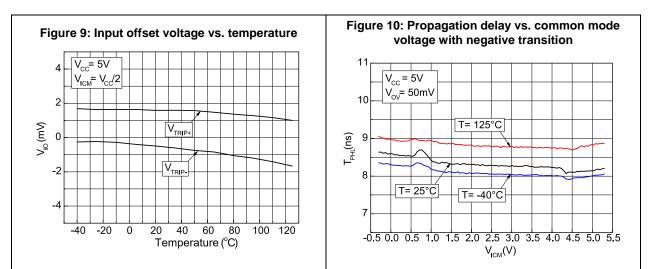


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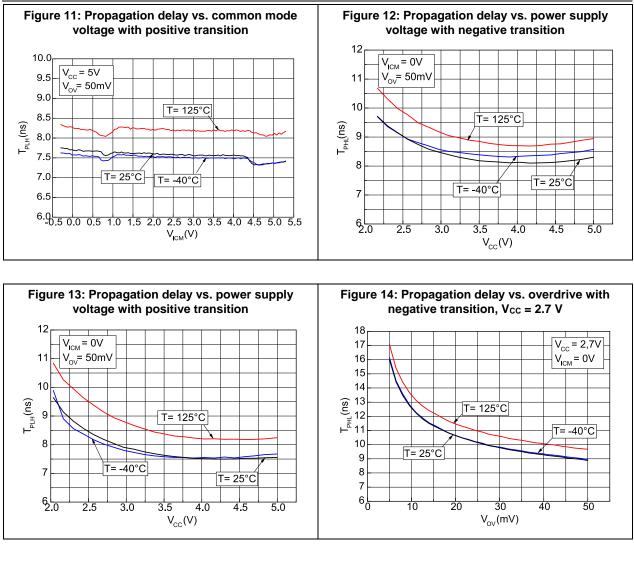
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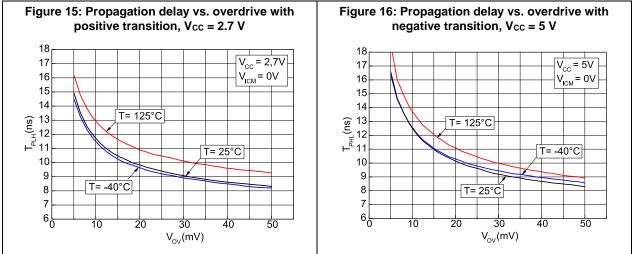


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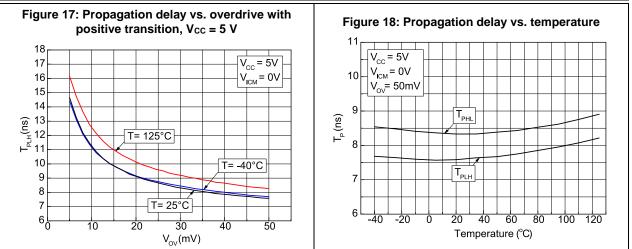




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Electrical characteristic curves



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5 Application recommendation

When high speed comparators are used, it is strongly recommended to place a capacitor as close as possible to the supply pins. Decoupling has two main advantages for this application: it helps to reduce electromagnetic interference and rejects the ripple that may appear on the output.

A bypass capacitor combination, composed of 100 nF in addition to 10 nF and 1 nF in parallel is recommended because it eliminates spikes on the supply line better than a single 100 nF capacitor. Each millimeter of the PCB track plays an important role. Bypass capacitors must be placed as close as possible to the comparator supply pin. The smallest value capacitor should be preferably placed closer to the supply pin.

In addition, important values of input impedance in series with parasitic PCB capacity and input comparator capacity create an additional RC filter. It generates an additional propagation delay.

For high speed signal applications, PCB must be designed with great care taking into consideration low resistive grounding, short tracks and quality SMD capacitors featuring low ESR. Bypass capacitor stores energy and provides a complementary energy tank when spikes occur on the power supply line. If the input signal frequency is far from the resonant frequency, impedance strongly increases and the capacitor loses bypassing capability. Placing different capacitors with different resonant frequencies allows a wide frequency bandwidth to be covered.

It is also recommended to implement an unbroken ground plane with low inductance.

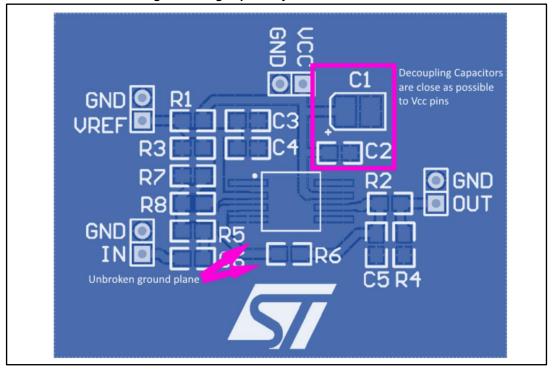


Figure 19: High speed layout recommendation

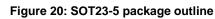


6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.



6.1 SOT23-5 package information



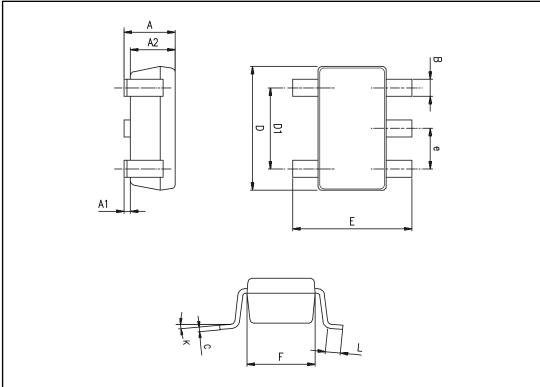
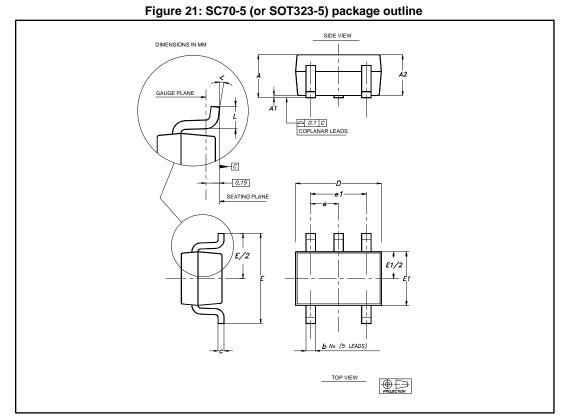


Table 6: SOT23-5 mechanical data

	Dimensions							
Ref.		Millimete	rs					
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	0.90	1.20	1.45	0.035	0.047	0.057		
A1			0.15			0.006		
A2	0.90	1.05	1.30	0.035	0.041	0.051		
В	0.35	0.40	0.50	0.014	0.016	0.020		
С	0.09	0.15	0.20	0.004	0.006	0.008		
D	2.80	2.90	3.00	0.110	0.114	0.118		
D1		1.90			0.075			
е		0.95			0.037			
E	2.60	2.80	3.00	0.102	0.110	0.118		
F	1.50	1.60	1.75	0.059	0.063	0.069		
L	0.10	0.35	0.60	0.004	0.014	0.024		
К	0 degrees		10 degrees	0 degrees		10 degrees		





	Dimensions							
Ref.		Millimeters						
	Min.	Тур.	Max.	Min.	Тур.	Max.		
А	0.80		1.10	0.032		0.043		
A1			0.10			0.004		
A2	0.80	0.90	1.00	0.032	0.035	0.039		
b	0.15		0.30	0.006		0.012		
С	0.10		0.22	0.004		0.009		
D	1.80	2.00	2.20	0.071	0.079	0.087		
E	1.80	2.10	2.40	0.071	0.083	0.094		
E1	1.15	1.25	1.35	0.045	0.049	0.053		
е		0.65			0.025			
e1		1.30			0.051			
L	0.26	0.36	0.46	0.010	0.014	0.018		
<	0°		8°	0°		8°		



6.3 DFN8 2x2 mm package information

Figure 22: DFN8 2x2 mm package outline

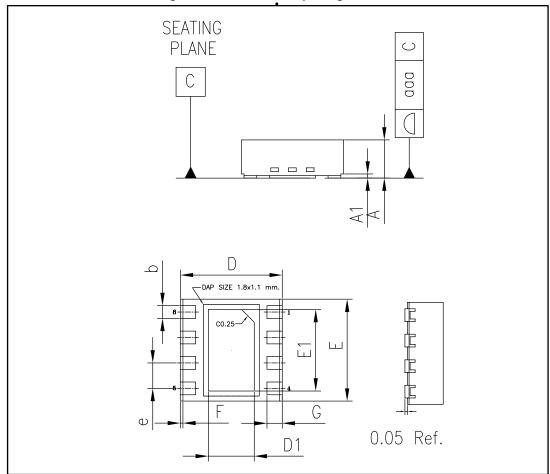


Table 8: DFN8 2x2 mm package mechanical data
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	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.70	0.75	0.80	0.027	0.029	0.031
A1		0.10			0.003	
b	0.20	0.25	0.30	0.007	0.009	0.011
D	1.95	2.00	2.05	0.076	0.078	0.080
D1	0.80	0.90	1.00	0.031	0.035	0.039
E	1.95	2.00	2.05	0.076	0.078	0.080
E1	1.50	1.60	1.70	0.059	0.062	0.066
е		0.50			0.019	
F		0.05			0.001	
G	0.25	0.30	0.35	0.009	0.011	0.013
aaa		0.10			0.003	



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7 Ordering information

Table 9: Order code								
Order code	Temperature range	Package	Packaging	Marking				
TS3011ILT		SOT23-5	Tape and reel	K540				
TS3011IYLT (1)	-40 °C to 125 °C			K541				
TS3011ICT		SC70-5		K54				
TS3011IYQ3T ⁽¹⁾		DFN8 2x2		K5N				

Notes:

⁽¹⁾ Qualified and characterized according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 and Q 002 or equivalent.



8 Revision history

Table 10: Document revision history

Date	Revision	Changes
03-Oct-2011	1	Initial release.
18-Feb-2014	2	Updated Table 8: Order codes to add the order code TS3011IYLT. Added: Automotive qualification among the Features in the cover page.
27-May-2016	3	Updated document layout Section 3: "Electrical characteristics": updated unit of "Input offset voltage drift" parameter to µV/°C (not mV/°C). Section 4: "Electrical characteristic curves": X-axes changed to mV (not V) in figures 15, 16, 17, and 18. Table 6: added "K" values for inches Table 7: updated A and A2 min values for inches and added "<" values for inches.
25-Aug-2017	4	Updated cover page image and description. Updated Figure 1: "Pin connections (top view)" and Table 9: "Order codes". Added Section 5.3: "TS3011 DFN package information".
07-Dec-2017	5	Updated Section 1: "Pin configuration". Added Section 5: "Application recommendation".



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